



Description

The HSBA4119 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

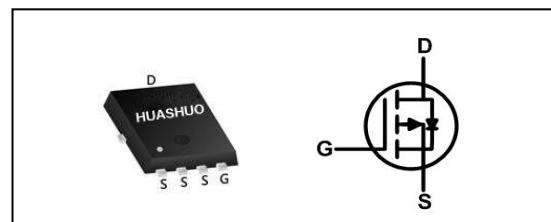
The HSBA4119 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

V _{DS}	-40	V
R _{DSON,typ}	3.1	mΩ
I _D	-120	A

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

PRPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-120	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ^{1,6}	-90	A
I _{DM}	Pulsed Drain Current ²	-580	A
EAS	Single Pulse Avalanche Energy ³	1250	mJ
I _{AS}	Avalanche Current	-70	A
P _D @T _C =25°C	Total Power Dissipation ⁴	150	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹ (t≤10S)	---	20	°C/W
	Thermal Resistance Junction-ambient ¹ (Steady State)	---	62	°C/W
R _{θJC}	Thermal Resistance Junction-case ¹		---	1.5 °C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-40	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-30A	---	3.1	3.8	mΩ
		V _{GS} =-4.5V , I _D =-20A	---	4.0	5.6	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	---	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-40V , V _{GS} =0V , T _J =25°C	---	---	-1	uA
		V _{DS} =-40V , V _{GS} =0V , T _J =125°C	---	---	-100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
R _g	Gate resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Q _g	Total Gate Charge (-10V)	V _{DS} =-20V , V _{GS} =-10V , I _D =-20A	---	190	---	nC
Q _{gs}	Gate-Source Charge		---	24	---	
Q _{gd}	Gate-Drain Charge		---	38	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-20V , V _{GS} =-10V , R _G =3Ω, I _D =-10A	---	18	---	ns
T _r	Rise Time		---	3.6	---	
T _{d(off)}	Turn-Off Delay Time		---	21	---	
T _f	Fall Time		---	39	---	
C _{iss}	Input Capacitance	V _{DS} =-20V , V _{GS} =0V , f=1MHz	---	10700	---	pF
C _{oss}	Output Capacitance		---	780	---	
C _{rss}	Reverse Transfer Capacitance		---	660	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-120	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-20A , T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A , di/dt=100A/μs , T _J =25°C	---	52	---	nS
Q _{rr}	Reverse Recovery Charge		---	128	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-40V,V_{GS}=-10V,L=0.5mH,I_{AS}=-70A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation
- 6.The maximum current rating is package limited.



Typical Characteristics

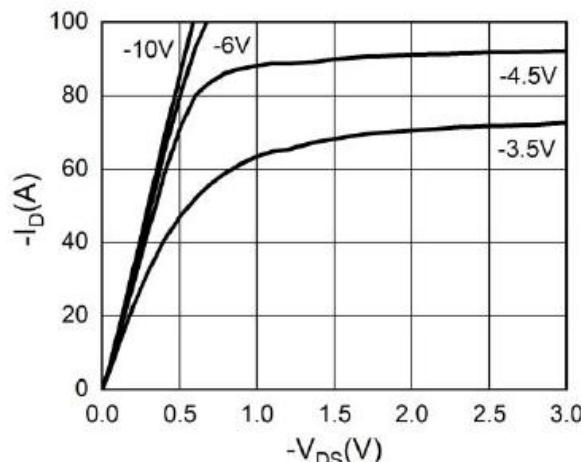


Fig.1 Output Characteristics

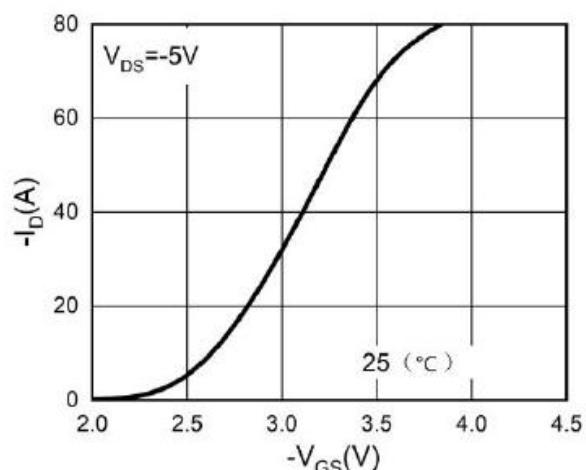


Fig.2 Transfer Characteristics

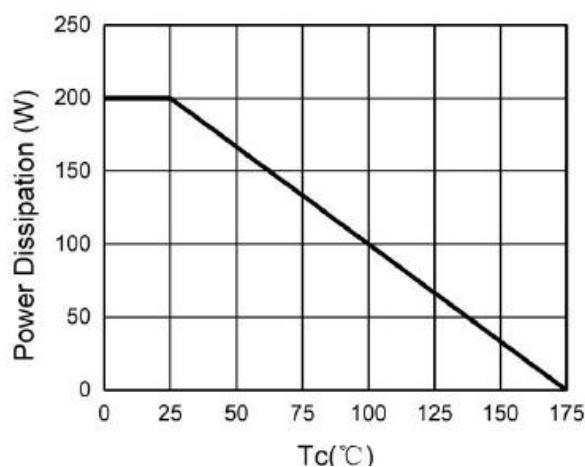


Fig.3 Power Dissipation

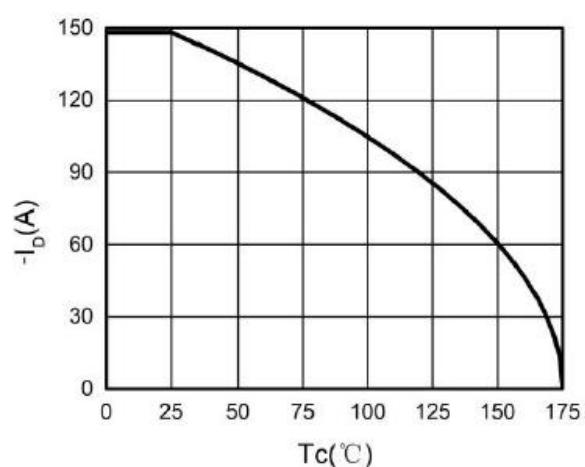


Fig.4 Drain Current

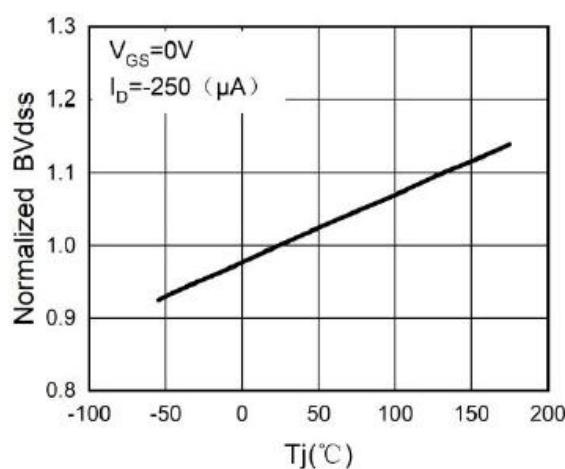


Fig.5 BV_{dss} vs Junction Temperature

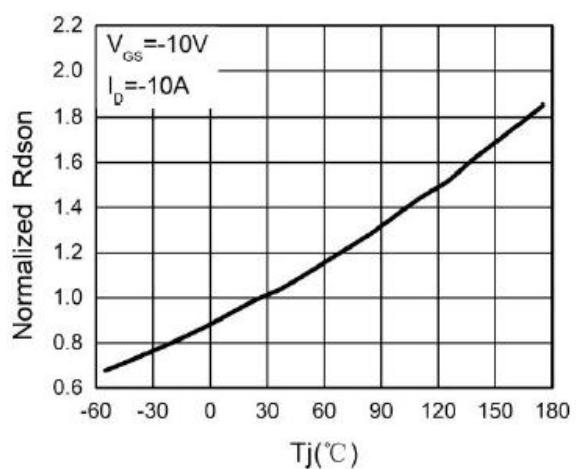


Fig.6 $R_{ds(on)}$ vs Junction Temperature



HUASHUO
SEMICONDUCTOR

HSBA4119

P-Ch 40V Fast Switching MOSFETs

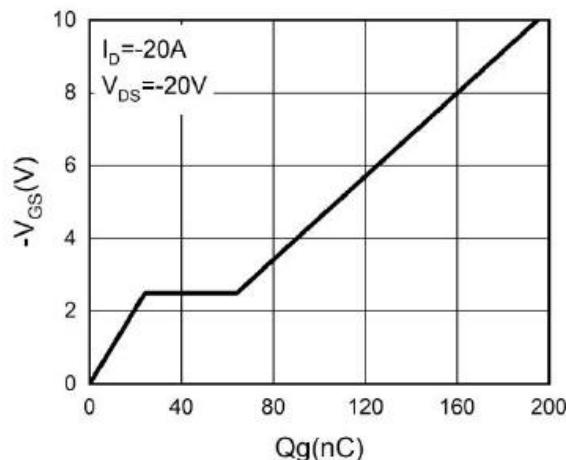


Fig.7 Gate Charge Waveforms

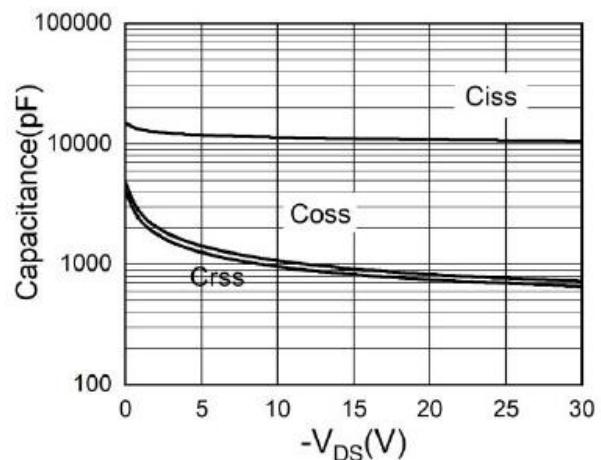


Fig.8 Capacitance

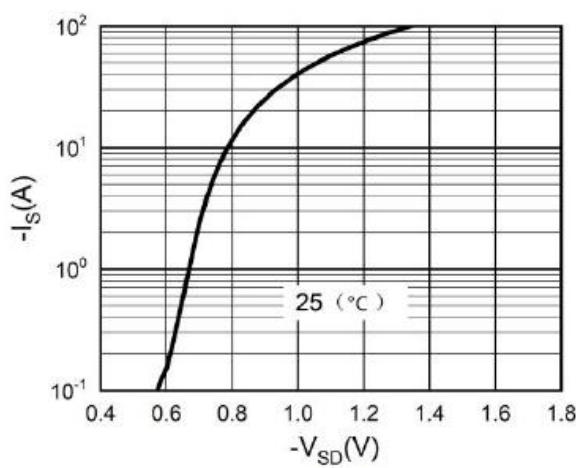


Fig.9 Body-Diode Characteristics

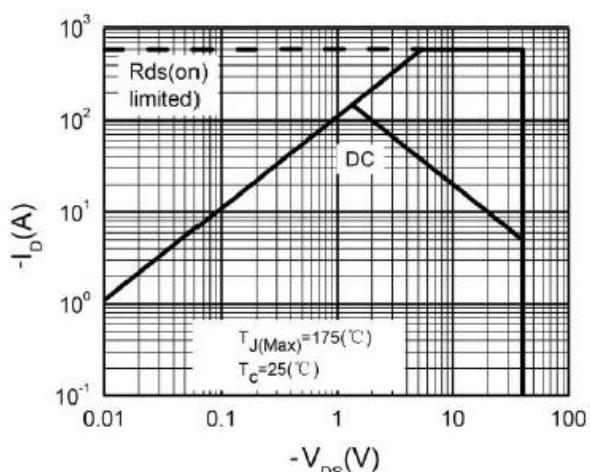
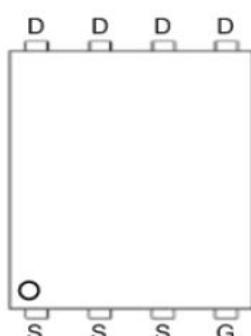
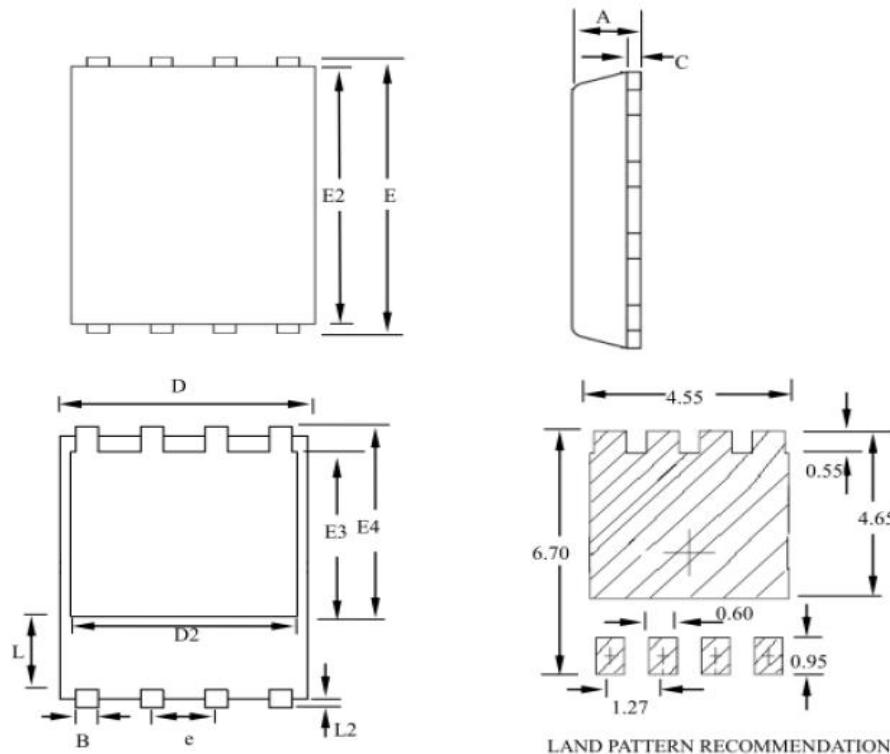


Fig.10 Maximum Safe Operating Area



Ordering Information

Part Number	Package code	Packaging
HSBA4119	PRPAK5*6	3000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--